MITSUBISHI SEMICONDUCTOR < Application Specific Intelligent Power Module>

PS11017

FLAT-BASE TYPE INSULATED TYPE

PS11017



INTEGRATED FUNCTIONS AND FEATURES

- 3-phase IGBT inverter bridge configured by the latest 3rd. generation IGBT and diode technologies.
- Circuit for dynamic braking of motor regenerative energy.
- Inverter output current capability Io (Note 1):

Type Name		100% load	150% over load		
	PS11017	17.0A (rms)	25.5A (rms), 1min		

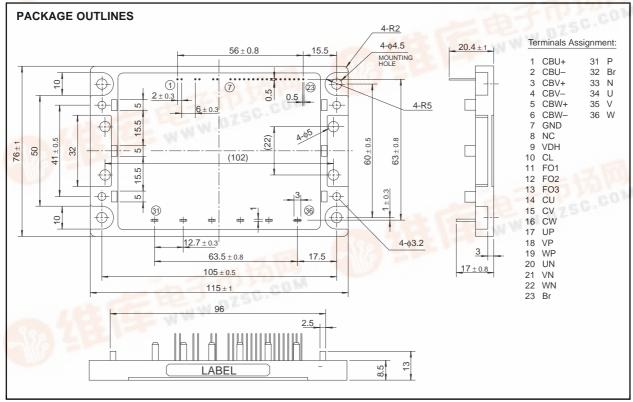
(Note 1) : The inverter output current is assumed to be sinusoidal and the peak current value of each of the above loading cases is defined as : $IOP = IO \times \sqrt{2}$

INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS:

- For P-Side IGBTs: Drive circuit, High voltage isolated high-speed level shifting, Short-circuit protection (SC), Bootstrap circuit supply scheme (Single drive-power-supply) and Under voltage protection (UV).
- For N-Side IGBTs: Drive circuit, Short circuit protection (SC), Control-supply Under voltage and Over voltage protection (OV/UV), System Over-temperature protection (OT), Fault output (Fo) signaling circuit, and Current-Limit warning signal output (CL)
- For Brake circuit IGBT : Drive circuit
- Warning and Fault signaling:
 - Fo1: Short circuit protection for lower-leg IGBTs and Input interlocking against spurious arm shoot-through.
 - Fo2: N-side control supply abnormality locking (OV/UV)
 - Fo3: System over-temperature protection (OT).
 - CL: Warning for inverter current overload condition
- For system feedback control : Analogue signal feedback reproducing actual inverter phase current (3φ).
- Input Interface: 5V CMOS/TTL compatible, Schmitt trigger input, and Arm-Shoot-Through interlock protection.

APPLICATION

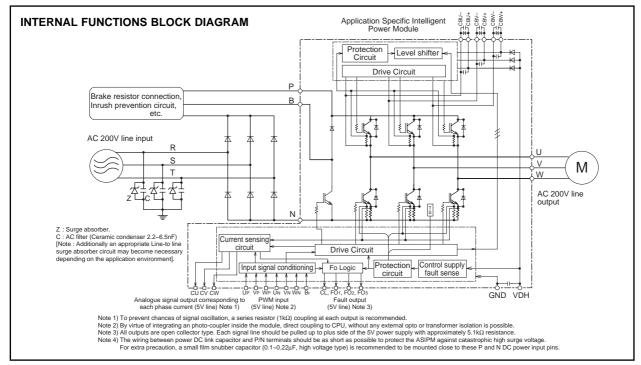
Acoustic noise-less 3.7kW/AC200V class 3 phase inverter and other motor control applications.







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(Fig. 2)

MAXIMUM RATINGS (Tj = 25°C) INVERTER PART (Including Brake Part)

Symbol	Item	Condition	Ratings	Unit
Vcc	Supply voltage	Applied between P-N	450	V
VCC(surge)	Supply voltage (surge)	Applied between P-N, Surge-value	500	V
VP or VN	Each output IGBT collector-emitter static voltage	Applied between P-U, V, W, Br or U, V, W, Br-N	600	V
VP(S) or VN(S)	Each output IGBT collector-emitter switching surge voltage	Applied between P-U, V, W, Br or U, V, W, Br-N	600	V
±IC(±ICP)	Each output IGBT collector current	Tc = 25°C	±50 (±100)	Α
IC(ICP)			15 (30)	Α
IF(IFP)	Brake diode anode current	Note: "()" means IC peak value	15 (30)	Α

CONTROL PART

Symbol	Item	Item Condition		Unit	
VDH, VDB	Supply voltage	Applied between VDH-GND, CBU+-CBU-, CBV+-CBV-, CBW+-CBW-	20	٧	
VCIN	Input signal voltage	Applied between UP · VP · WP · UN · VN · WN · Br-GND	-0.5 ~ 7.5	٧	
VFO	Fault output supply voltage	Applied between Fo1 · Fo2 · Fo3-GND	− 0.5 ~ 7	V	
IFO	Fault output current	Sink current of F01 · F02 · F03	15	mA	
VCL	Current-limit warning (CL) output voltage	Applied between CL-GND	− 0.5 ~ 7	V	
ICL	CL output current	Sink current of CL	15	mA	
Ico	Analogue current signal output current	Sink current of CU · CV · CW	±1	mA	



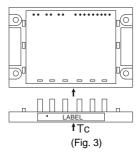
FLAT-BASE TYPE INSULATED TYPE

TOTAL SYSTEM

Symbol	Item	Condition	Ratings	Unit
Tj	Junction temperature	(Note 2)	−20 ~ +125	°C
Tstg	Storage temperature	_	-40 ~ + 125	°C
Тс	Module case operating temperature	(Fig. 3)	−20 ~ +100	°C
Viso	Isolation voltage	60 Hz sinusoidal AC applied between all terminals and the base plate for 1 minute.	2500	Vrms
	Mounting torque	Mounting screw: M4.0	0.98 ~ 1.47	N⋅m

Note 2) The item defines the maximum junction temperature for the power elements (IGBT/Diode) of the ASIPM to ensure safe operation. However, these power elements can endure instantaneous junction temperature as high as 150°C instantaneously. To make use of this additional temperature allowance, a detailed study of the exact application conditions is required and, accordingly, necessary information is requested to be provided before use.

CASE TEMPERATURE MEASUREMENT POINT (3mm from the base surface)



THERMAL RESISTANCE

0	Item	Condition	Ratings			
Symbol			Min.	Тур.	Max.	Unit
Rth(j-c)Q		Inverter IGBT (1/6)	_	_	1.75	°C/W
Rth(j-c)F	Junction to case Thermal Resistance	Inverter FWDi (1/6)	_	_	2.4	°C/W
Rth(j-c)Q		Brake IGBT	_	_	2.9	°C/W
Rth(j-c)F		Brake FWDi	_	_	4.5	°C/W
Rth(c-f)	Contact Thermal Resistance	Case to fin, thermal grease applied	_	_	0.031	°C/W

ELECTRICAL CHARACTERISTICS (Tj = 25°C, VDH = 15V, VDB = 15V unless otherwise noted)

Symbol	l Item	Condition		Ratings			
Symbol	item	Condition	Min.	Тур.	Max.	Unit	
VCE(sat)	Collector-emitter saturation voltage	VDH = VDB = 15V, Input = ON, Tj = 25°C, Ic = 50A	_	_	2.9	V	
VEC	FWDi forward voltage	Tj = 25° C, Ic = $-50A$, Input = OFF	_	_	2.9	V	
VCE(sat)Br	Brake IGBT Collector-emitter saturation voltage	VDH = 15V, Input = ON, Tj = 25°C, Ic = 15A	_	_	3.5	٧	
VFBr	Brake diode forward voltage	Tj = 25°C, IF = 15A, Input = OFF	_	_	2.9	V	
ton		1/2 Bridge inductive, Input = ON	0.40	0.8	2.0	μs	
tc(on)	Switching times	Vcc = 300V, Ic = 50A, Tj = 125°C	_	0.40	1.0	μs	
toff	Switching times	VDH = 15V, VDB = 15V		1.5	2.4	μs	
tc(off)		Note : ton, toff include delay time of the internal control	_	0.6	1.3	μs	
trr	FWD reverse recovery time	circuit	_	0.15	_	μs	
	Short circuit endurance Vcc ≤ 400V, Input = ON (one-shot)		• No destruction				
	(Output, Arm, and Load,	Tj = 125°C start	No destructionFo output by protection operation				
	Short Circuit Modes)	13.5V ≤ VDH = VDB ≤ 16.5V					
		Vcc ≤ 400V, Tj ≤ 125°C,	No destruction No protecting operation				
	Switching SOA	Ic < IoL(CL) operation level, Input = ON,					
		13.5V ≤ VDH = VDB ≤ 16.5V	No Fo output				
IDН	Circuit current	VDH = 15V, VCIN = 5V	_	_	150	mA	
Vth(on)	Input on threshold voltage		0.8	1.4	2.0	V	
Vth(off)	Input off threshold voltage		2.5	3.0	4.0	V	
Ri	Input pull-up resister	Integrated between input terminal-VDH	_	150	_	kΩ	



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ELECTRICAL CHARACTERISTICS (Tj = 25°C, VDH = 15V, VDB = 15V unless otherwise noted)

Cumbal	Item		Condition		Ratings			Unit	
Symbol					Min.	Тур.	Max.		
fPWM	PWM input frequency		Tc ≤ 100°C, Tj ≤ 125°C			_	15	kHz	
txx	Allowable input on-pulse w		$VDH = 15V, TC = -20^{\circ}C$	C ~ +100°C	(Note 3)	1	_	500	μs
tdead	Allowable input signal dead blocking arm shoot-through		Relates to correspondi (Except brake part), To		100°C	2.5	_	_	μs
tint	Input inter-lock sensing		Relates to corresponding	input (Except b	reak part)	_	65	100	ns
Vco			Ic = 0A	VDH = 15V		1.87	2.27	2.57	V
Vc+(200%)	Analogue signal linearity with	output current	Ic = IOP(200%)	Tc = -20°C	~ 100°C	0.77	1.17	1.47	V
Vc-(200%)			Ic = -Iop(200%)		(Fig. 4)	2.97	3.37	3.67	V
ΔVco	Offset change area vs tem	perature	VDH = 15V, TC = −20°C	~ 100°C		_	15	_	mV
VC+			Ic > IOP(200%), VDH =	15V			_	0.7	V
Vc-	Analogue signal output voltage limit				(Fig. 4)	4.0	_	_	V
ΔVc(200%)	Analogue signal over all linear variation		Vco-Vc±(200%)		, ,		1.1		V
rCH	Analogue signal data hold accuracy		Correspond to max. 50 only, Ic = IOP(200%)	0μs data hold	period (Fig. 5)	- 5	_	5	%
td(read)	Analogue signal reading time		After input signal trigge	r point	(Fig. 8)	_	3	_	μs
ICL(H)	Signal output current of	Idle			_	_	1	μΑ	
ICL(L)	CL operation	Active	Open collector output			_	1	_	mA
±lol	CL warning operation level		VD = 15V, TC = −20°C	~ 100°C	(Note 4)	48.2	60.0	72.0	Α
SC	Short circuit over current tr	ip level	Tj = 25°C	(Fig. 7) (Note 5)	79.2	102	_	Α
OT	Over temperature	Trip level	\/D\\ 45\/			100	110	120	°C
OTr	protection	Reset level	VDH = 15V			90		°C	
UVDH		Trip level				11.05	12.00	12.75	V
UVDHr		Reset level				11.55	12.50	13.25	V
OVDH		Trip level				18.00	19.20	20.15	V
OVDHr	Supply circuit under &	Reset level	$Tc = -20 \sim +100^{\circ}C$			16.50	17.50	18.65	V
UVDB	over voltage protection	Trip level	- Tj ≤ 125°C			10.0	11.0	12.0	V
UVDBr		Reset level				10.5	11.5	12.5	V
tdV		Filter time				_	10	_	μs
IFO(H)	Foult output ourront	Idle	0			_	_	1	μA
IFO(L)	Fault output current	Active	Open collector output				1		mA

(Note 3): (a) Allowable minimum input on-pulse width: This item applies to P-side circuit only.

(b) Allowable maximum input on-pulse width: This item applies to both P-side and N-side circuits excluding the brake circuit. (Note4): CL output: The "current limit warning (CL) operation circuit outputs warning signal whenever the arm current exceeds this limit. The circuit is reset automatically by the next input signal and thus, it operates on a pulse-by-pulse scheme.

(Note5): The short circuit protection works instantaneously when a high short circuit current flows through an internal IGBT rising up momentarily. The protection function is, thus meant primarily to protect the ASIPM against short circuit distraction. Therefore, this function is not recommended to be used for any system load current regulation or any over load control as this might, cause a failure due to excessive temperature rise. Instead, the analogue current output feature or the over load warning feature (CL) should be appropriately used for such current regulation or over load control operation. In other words, the PWM signals to the ASIPM should be shut down, in principle, and not to be restarted before the junction temperature would recover to normal, as soon as a fault is feed back from its Fo1 pin of the ASIPM indicating a short circuit situation.

RECOMMENDED CONDITIONS

Symbol	Item	Condition	Ratings	Unit
Vcc	Supply voltage	Applied across P-N terminals	400 (max.)	V
VDH, VDB	Control Supply voltage	Applied between VDH-GND, CBU+-CBU-, CBV+-CBV-, CBW+-CBW-	15±1.5	V
ΔVDH, ΔVDB	Supply voltage ripple		±1 (max.)	V/μs
VCIN(on)	Input on voltage		0 ~ 0.3	V
VCIN(off)	Input off voltage		4.8 ~ 5.0	V
fPWM	PWM Input frequency	Using application circuit	2 ~ 15	kHz
tdead	Arm shoot-through blocking time	Using application circuit	2.5 (min.)	μs



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Fig. 4 OUTPUT CURRENT ANALOGUE SIG-NALING LINEARITY

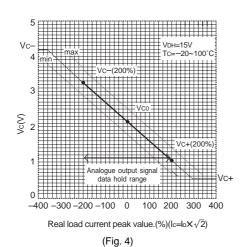
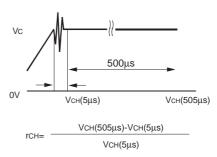
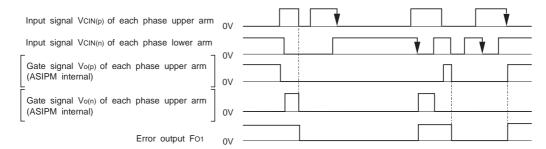


Fig. 5 OUTPUT CURRENT ANALOGUE SIGNALING "DATA HOLD" DEFINITION



Note; Ringing happens around the point where the signal output voltage changes state from "analogue" to "data hold" due to test circuit arrangement and instrumentational trouble. Therefore, the rate of change is measured at a 5 µs delayed point.

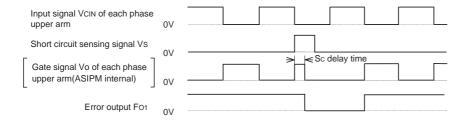
Fig. 6 INPUT INTERLOCK OPERATION TIMING CHART



Note: Input interlock protection circuit; It is operated when the input signals for any upper-arm / lower-arm pair of a phase are simultaneously in "LOW" level.

By this interlocking, both upper and lower IGBTs of this mal-triggered phase are cut off, and "Fo" signal is outputted. After an "input interlock" operation the circuit is latched. The "Fo" is reset by the high-to-low going edge of either an upper-leg, or a lower-leg input, whichever comes in later.

Fig. 7 TIMING CHART AND SHORT CIRCUIT PROTECTION OPERATION



Note: Short circuit protection operation. The protection operates with "Fo" flag and reset on a pulse-by-pulse scheme. The protection by gate shutdown is given only to the IGBT that senses an overload (excluding the IGBT for the "Brake").



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Fig. 8 INVERTER OUTPUT ANALOGUE CURRENT SENSING AND SIGNALING TIMING CHART

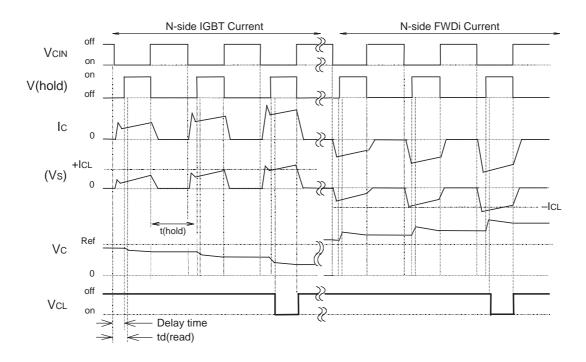


Fig. 9 START-UP SEQUENCE

Normally at start-up, Fo and CL output signals will be pulled-up High to Supply voltage (OFF level); however, Fo1 output may fall to Low (ON) level at the instant of the first ON input pulse to an N-Side IGBT. This can happen particularly when the boot-strap capacitor is of large size. Fo1 resetting sequence (together with the boot-strap charging sequence) is explained in the following graph

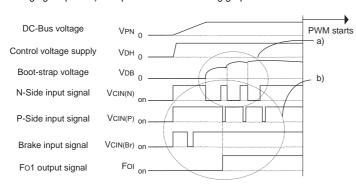
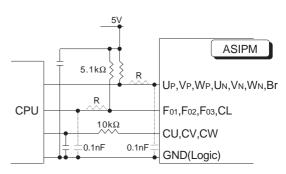


Fig. 10 RECOMMENDED I/O INTERFACE CIRCUIT



a) Boot-strap charging scheme :

Apply a train of short ON pulses at all N-IGBT input pins for adequate charging (pulse width = approx. 20μs number of pulses =10 ~ 500 depending on the boot-strap capacitor size)

b) Fo1 resetting sequence:

Apply ON signals to the following input pins : Br \to Un/Vn/Wn \to Up/Vp/Wp in that order.